Optical Emitter and Sensor Pair

OPB100Z, OPB100-EZ, OPB100-SZ



Features:

- Infrared LED emitter
- Silicon phototransistor sensor
- Snap-in mounting
- Variable sensing distance over 36" (91.4 cm)
- Low profile package
- 24" (61.0 cm) wire leads



Description:

The **OPB100Z** series consists of an infrared LED (**OPB100-EZ**) and phototransistor (**OPB100-SZ**) in separate plastic housings. The low cost, snap-in design requires no screws or other mounting hardware for ease of installation.

The emitter and sensor are not apertured, which allows separation distances in excess of 36" (91.4 cm) without concern for precise alignment. The front side clip allows mounting of the product to any 0.059" (1.50 mm) thick material.

This product is designed for general switching and low-speed data communications applications.

Applications:

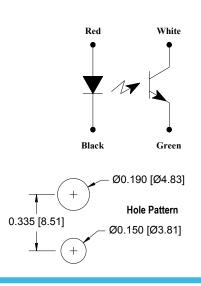
- Non-contact reflective object
- Non-contact interruptive sensing

Emitter (LED)

- Assembly line automation
- Machine automation
- Machine safety

	Ordering Information						
Part Number	LED Peak Wavelength	Sensor	Lead Length / Spacing				
OPB100-EZ	880 nm		24" / 26 AWG				
OPB100-SZ		Transistor	Wire				
OPB100Z	Contains both	Z & OPB100-SZ					

GREEN WIRE EMITTER **Phototransistor** 0.20 24" Min. WHITE WIRE COLLECTOR **RED WIRE** ANODE Ø.184±.006 Ø0.18 BLACK WIRE -.335±.005 Hole Pattern Ø0.140±0.005 **Hole Pattern** SNAP BODY $2 \text{X.061}^{+.002}_{-.001}$ 0.11 0.34±0.015 **26 AWG** Symbolize Cover 0.32 **UL Rated**



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Absolute Maximum Ratings (T _A = 25° C unless otherwise noted)										
Storag	-40° C to +85° C									
Opera		-40° C to +80° C								
Input LED (OP298 for additional information)										
Forwa	Forward DC Current									
Peak F	Peak Forward Current (1 μs pulse width, 300 pps)									
Revers	Reverse DC Voltage									
Power	Power Dissipation ⁽²⁾									
Output Phototransistor (OP598 for additional information)										
Collect	Collector-Emitter Voltage									
Emitte	Emitter-Collector Voltage									
Collect	Collector DC Current									
Power	250 mW									
Electrical Characteristics (T _A = 25° C unless otherwise noted)										
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS				
Input Diode (See OP298 for additional information — for reference only)										
V _F	Forward Voltage		-	1.7	V	I _F = 20 mA				
I _R	Reverse Current	-	-	15	μΑ	V _R = 10 V				
Q _{HP}	Emission Angle at Half Power Points	-	25	-	Degree	I _F = 20 mA				
E _E (APT)	Apertured Radiant Intensity	6.5	-	-	mW/ cm²	I _F = 100 mA Distance = 1.43" (3.63 cm) Aperture = 0.25" (6.35 mm)				
Output Phototransistor (See OP598 for additional information — for reference only)										
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage		-	-	V	$I_C = 1 \text{ mA}, E_E = 0 \text{mw/cm}^2 \text{ (no light)}$				
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	5	-	-	V	$I_C = 100 \mu A$, $E_E = 0 \text{mw/cm}^2$ (no light)				
I _{CEO} Collector Dark Current		-	-	100	nA	$V_{CE} = 10V, I_F = 0, E_E = 0 \text{ mw/cm}^2$ (no light)				
V _{CE(SAT)}	V _{CE(SAT)} Collector-Emitter Saturation Voltage		-	0.4	V	$I_C = 400 \mu A, E_E = 1.7 \text{ mw/cm}^2$				
I _{C(ON)} On-State Collector Current		5	-	-	mA	V _{CE} = 5 V, E _E =	= 1.7 mw/cm ²			

Notes:

- 1. Derate linearly 3.33 mW/°C above 25°C.
- 2. All parameters measured using pulse technique.
- Derate linearly 1.43 mW/°C above 25°C.

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Performance Output Current vs. Distance

